Unit in mm

GTR Module

Silicon N Channel IGBT

High Power Switching Applications Motor Control Applications

Features

• High input impedance

• High speed:

 $t_f = 1.0 \mu s (Max.)$

 $t_{rr} = 0.5 \mu s \, (Max.)$

· Low saturation:

 $V_{CE (sat)} = 2.7V (Max.)$

Enhancement mode

• The electrodes are isolated from case

Includes a complete half bridge card in one package

Maximum Ratings (Ta = 25°C)

CHARACTERISTICS		SYMBOL	RATING	TINU	
Collector-Emitter Voltage		V _{CES}	1200	٧	
Gate-Emitter Voltage		V _{GES}	± 20	٧	
Collector Current	DC	lc	50	А	
	1ms	I _{CP}	100		
Forward Current	DC	Ι _F	50	_ A	
	1ms	¹ FM	100	A	
Collector Power Dissipation (Tc = 25°C)		P _C	400	w	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	-40 ~ 125	ů	
Isolation Voltage		V _{isol}	2500 (AC 1 min.)	٧	
Screw Torque (Terminal/Mounting)			3/3	N¥m	

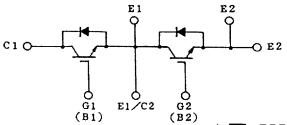
3-M5 B2 2-Ø5.6±0.3 3-M5 E2 2-Ø5.6±0.3 2-Ø5.6±0.3 3-M5 E1 4±0.5 23±0.5 B1 27±0.5 4±0.5 4±0.5 9.9±0.8 27±0.5 4±0.5 19±0.5 18±0.5 91±0.5 33.3±0.5

2 - 9 4 D 1 A

Weight: 202g

JEDEC EIAJ TOSHIBA

Equivalent Circuit



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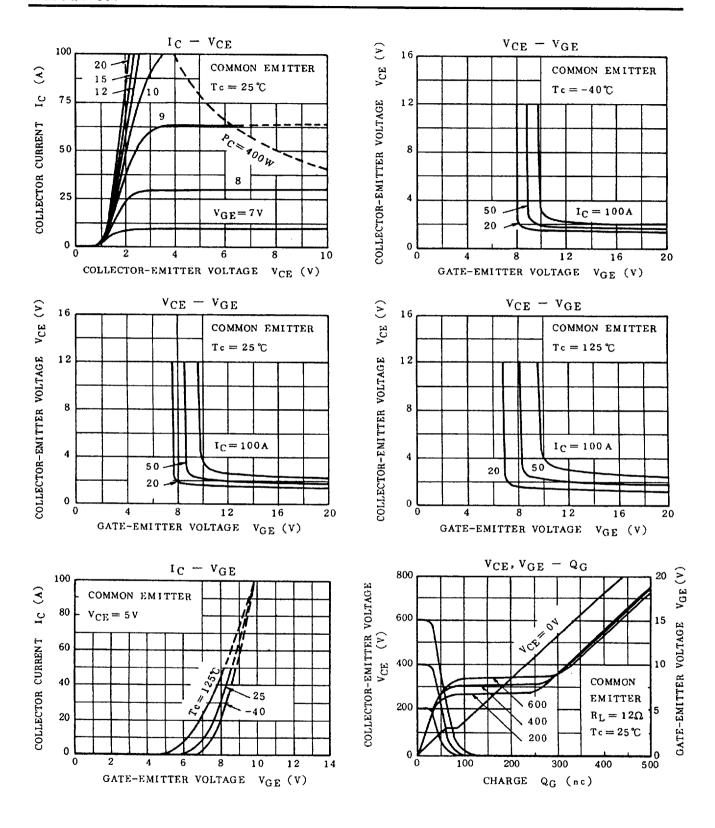
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Electrical Characteristics (Ta = 25°C)

СН	ARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I _{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$			± 500	nA
Collector Cut-off Current		I _{CES}	V _{CE} = 1200V, V _{GE} = 0	_		1.0	mA
Gate-Emitter Cut-off Voltage		V _{GE (OFF)}	I _C = 50mA, V _{CE} = 5V	3.0	_	6.0	٧
Collector-Emit	ter Saturation Voltage	V _{CE (sat)}	I _C = 50A, V _{GE} = 15V	_	2.2	2.7	٧
Input Capacita	nce	C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz	_	7800		pF
Switching Time	Rise Time	t _r	15V 24Ω G		0.3	0.6	μs
	Turn-on Time	t _{on}			0.4	0.8	
	Fall Time	t _f		_	0.6	1.0	
	Turn-off Time	t _{off}			1.2	1.8	
Forward Voltage		V _F	I _F = 50A, V _{GE} = 0		2.0	2.5	٧
Reverse Recovery Time		t _{rr}	I _F = 50A, V _{GE} = -10V di/dt = 100A/μs	_	0.25	0.5	μs
Thermal Resistance		P	Transistor		_	0.31	2004
		R _{th (j - c)}	Diode	_		1.0	•C/W

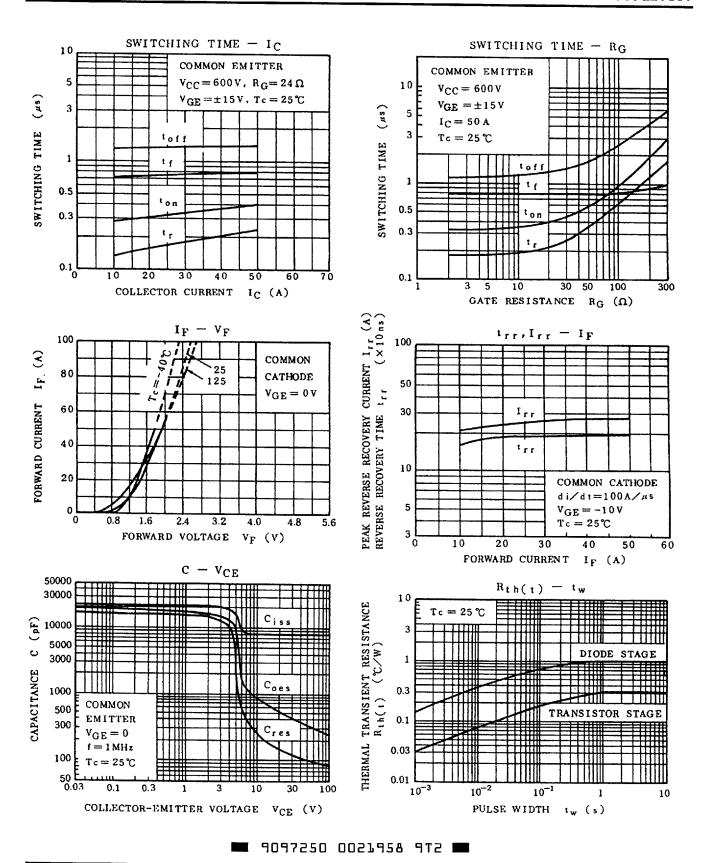
Note 1 : Do not apply the over rating voltage.



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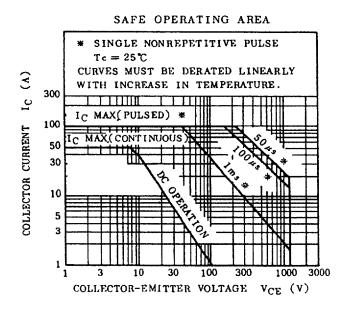
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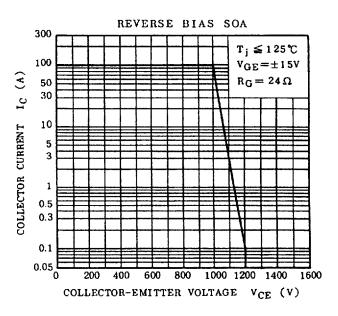


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